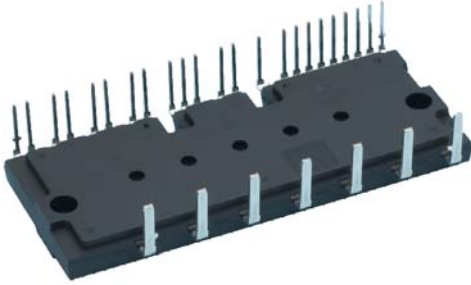


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OUTLINE



MAIN FEATURES AND RATINGS

- 3 phase DC/AC inverter
- 1200V / 25A
- Built-in LPT-CSTBT (5th generation IGBT)
- Insulated transfer molding package
- N-side IGBT open emitter

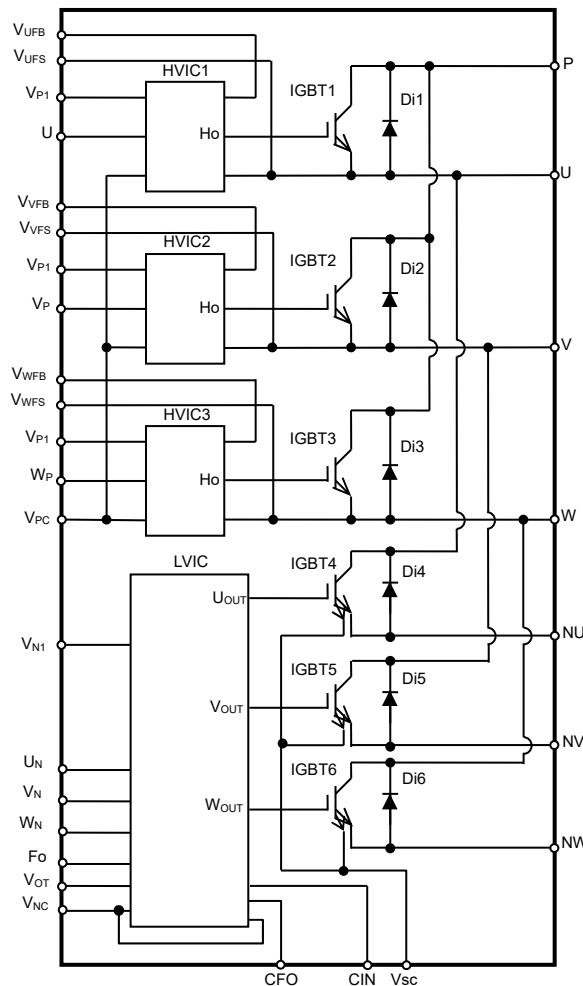
APPLICATION

- AC 400V class motor control

INTEGRATED DRIVE, PROTECTION AND SYSTEM CONTROL FUNCTIONS

- For P-side : Drive circuit, High voltage high-speed level shifting, Control supply under-voltage (UV) protection
- For N-side : Drive circuit, Control supply under-voltage protection (UV), Short circuit protection (SC)
- Fault signaling : Corresponding to SC fault (N-side IGBT), UV fault (N-side supply)
- Temperature output : Outputting LVIC temperature by analog signal
- Input interface : 5V line, Schmitt trigger receiver circuit (High Active)
- UL Recognized : UL1557 File E80276

INTERNAL CIRCUIT



MAXIMUM RATINGS ($T_j = 25^\circ\text{C}$, unless otherwise noted)

INVERTER PART

Symbol	Parameter	Condition	Ratings	Unit
V_{CC}	Supply voltage	Applied between P-NU,NV,NW	900	V
$V_{CC(\text{surge})}$	Supply voltage (surge)	Applied between P-NU,NV,NW	1000	V
V_{CES}	Collector-emitter voltage		1200	V
$\pm I_C$	Each IGBT collector current	$T_C = 25^\circ\text{C}$	25	A
$\pm I_{CP}$	Each IGBT collector current (peak)	$T_C = 25^\circ\text{C}$, up to 1ms	50	A
P_C	Collector dissipation	$T_C = 25^\circ\text{C}$, per 1 chip	113.6	W
T_j	Junction temperature		-20~+150	$^\circ\text{C}$

CONTROL (PROTECTION) PART

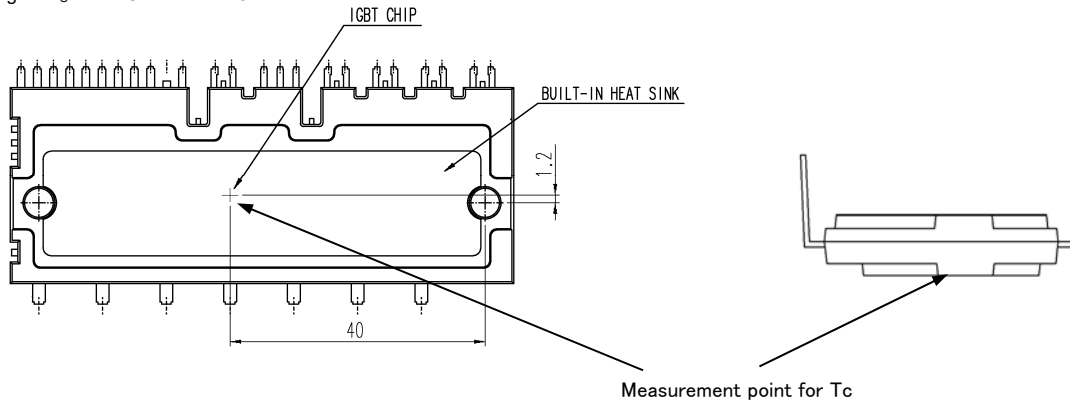
Symbol	Parameter	Condition	Ratings	Unit
V_D	Control supply voltage	Applied between $V_{P1}-V_{PC}$, $V_{N1}-V_{NC}$	20	V
V_{DB}	Control supply voltage	Applied between $V_{UFB}-V_{UFS}$, $V_{VFB}-V_{VFS}$, $V_{WFB}-V_{WFS}$	20	V
V_{IN}	Input voltage	Applied between U_P , V_P , W_P-V_{PC} , U_N , V_N , W_N-V_{NC}	-0.5~ $V_D+0.5$	V
V_{FO}	Fault output supply voltage	Applied between F_O-V_{NC}	-0.5~ $V_D+0.5$	V
I_{FO}	Fault output current	Sink current at F_O terminal	1	mA
V_{SC}	Current sensing input voltage	Applied between $CIN-V_{NC}$	-0.5~ $V_D+0.5$	V

TOTAL SYSTEM

Symbol	Parameter	Condition	Ratings	Unit
$V_{CC(\text{PROT})}$	Self protection supply voltage limit (Short circuit protection capability)	$V_D = 13.5\sim 16.5\text{V}$, Inverter Part $T_j = 125^\circ\text{C}$, non-repetitive, up to 2 μs	800	V
T_C	Module case operation temperature	(Note 1)	-20~+100	$^\circ\text{C}$
T_{stg}	Storage temperature		-40~+125	$^\circ\text{C}$
V_{iso}	Isolation voltage	60Hz, Sinusoidal, AC 1min, between connected all pins and heat sink plate	2500	V_{rms}

Note 1: T_c measurement point is described in Fig. 1.

Fig. 1: T_c MEASUREMENT POINT



THERMAL RESISTANCE

Symbol	Parameter	Condition	Limits			Unit
			Min.	Typ.	Max.	
$R_{\text{th}(l-c)Q}$	Junction to case thermal resistance (Note 2)	Inverter IGBT part (per 1/6 module)	-	-	0.88	K/W
$R_{\text{th}(l-c)F}$		Inverter FWDi part (per 1/6 module)	-	-	1.40	K/W

Note 2: Grease with good thermal conductivity and long-term endurance should be applied evenly with about +100 μm ~+200 μm on the contacting surface of DIIPM and heat sink. The contacting thermal resistance between DIIPM case and heat sink $R_{\text{th}(c-f)}$ is determined by the thickness and the thermal conductivity of the applied grease. For reference, $R_{\text{th}(c-f)}$ is about 0.2K/W (per 1/6 module, grease thickness: 20 μm , thermal conductivity: 1.0W/m \cdot k).

ELECTRICAL CHARACTERISTICS ($T_j = 25^\circ\text{C}$, unless otherwise noted)**INVERTER PART**

Symbol	Parameter	Condition	Limits			Unit	
			Min.	Typ.	Max.		
$V_{CE(sat)}$	Collector-emitter saturation voltage	$V_D=V_{DB} = 15\text{V}$, $V_{IN}= 5\text{V}$, $I_C= 25\text{A}$	$T_j= 25^\circ\text{C}$	-	1.90	2.60	V
			$T_j= 125^\circ\text{C}$	-	2.00	2.70	
V_{EC}	FWDi forward voltage	$V_{IN}= 0\text{V}$, $-I_C= 25\text{A}$	-	2.20	2.80	V	
t_{on}	Switching times	$V_{CC}= 600\text{V}$, $V_D= V_{DB}= 15\text{V}$ $I_C= 25\text{A}$, $T_j= 125^\circ\text{C}$, $V_{IN}= 0\leftrightarrow 5\text{V}$ Inductive Load (upper-lower arm)		0.50	1.20	1.90	μs
$t_{C(on)}$				-	0.60	0.90	μs
t_{off}				-	2.40	3.50	μs
$t_{C(off)}$				-	0.60	0.90	μs
t_{tr}				-	0.50	-	μs
I_{CES}	Collector-emitter cut-off current	$V_{CE}=V_{CES}$	$T_j= 25^\circ\text{C}$	-	-	1	mA
			$T_j= 125^\circ\text{C}$	-	-	10	

CONTROL (PROTECTION) PART

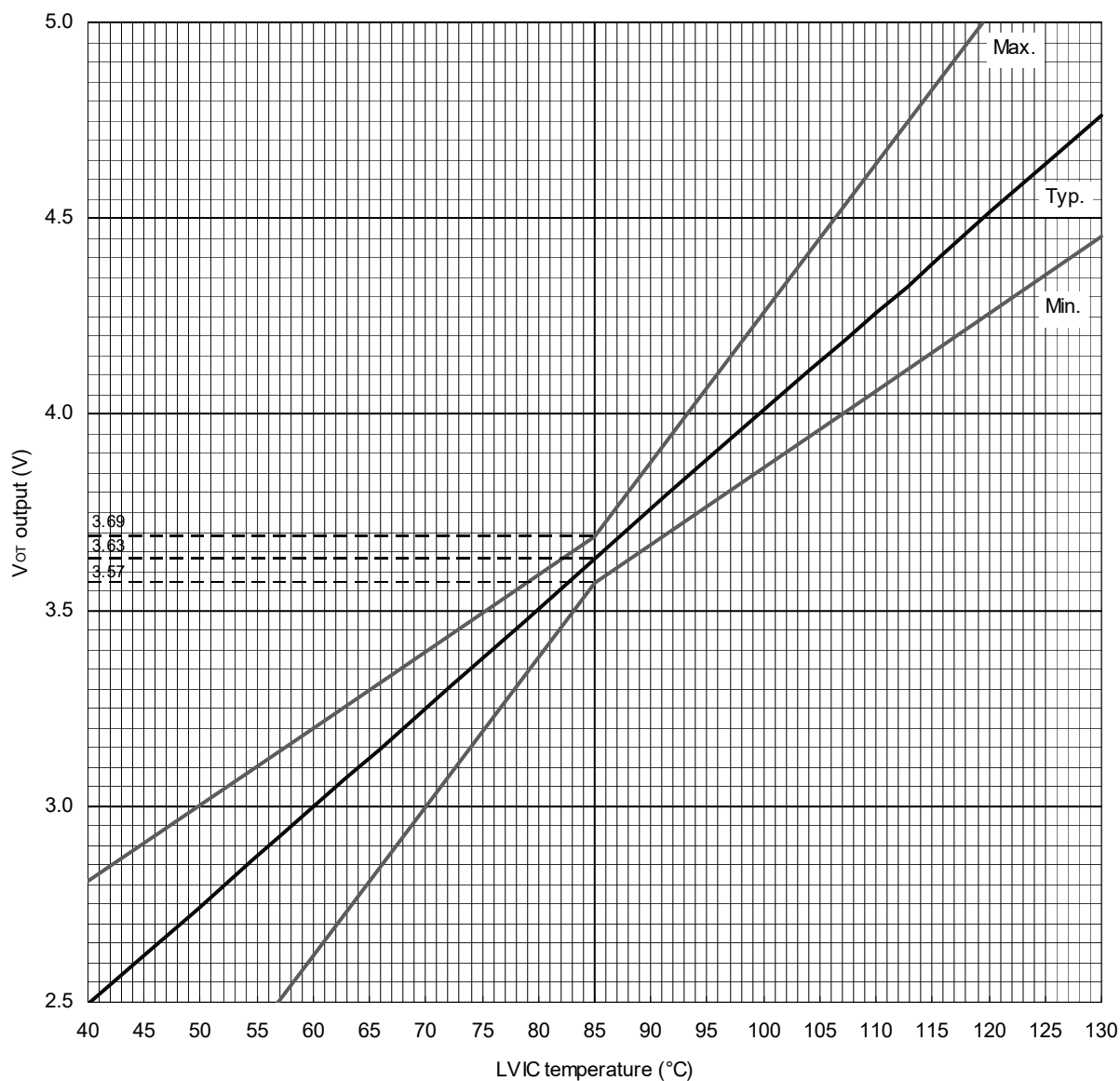
Symbol	Parameter	Condition	Limits			Unit	
			Min.	Typ.	Max.		
I_D	Circuit current	Total of $V_{P1}-V_{PC}$, $V_{N1}-V_{NC}$	$V_D=15\text{V}$, $V_{IN}=0\text{V}$	-	-	5.60	mA
			$V_D=15\text{V}$, $V_{IN}=5\text{V}$	-	-	5.60	
I_{DB}		Each part of $V_{UFB}-V_{UFS}$, $V_{VFB}-V_{VFS}$, $V_{WFB}-V_{WFS}$	$V_D=V_{DB}=15\text{V}$, $V_{IN}=0\text{V}$	-	-	1.10	
			$V_D=V_{DB}=15\text{V}$, $V_{IN}=5\text{V}$	-	-	1.10	
I_{SC}	Short circuit trip level	$-20^\circ\text{C}\leq T_j\leq 125^\circ\text{C}$, $R_s= 82.5\Omega (\pm 1\%)$, Not connecting outer shunt resistors to NU, NV, NW terminals (Note 3)	42.5	-	-	A	
UV_{DBt}	P-side Control supply under-voltage protection(UV)	$T_j\leq 125^\circ\text{C}$	Trip level	10.0	-	12.0	V
UV_{DBr}			Reset level	10.5	-	12.5	V
UV_{Dt}	N-side Control supply under-voltage protection(UV)	$T_j\leq 125^\circ\text{C}$	Trip level	10.3	-	12.5	V
UV_{Dr}			Reset level	10.8	-	13.0	V
V_{FOH}	Fault output voltage	$V_{SC} = 0\text{V}$, F_O terminal pulled up to 5V by 10k Ω	4.9	-	-	V	
V_{FOL}		$V_{SC} = 1\text{V}$, $I_{FO} = 1\text{mA}$	-	-	0.95	V	
t_{FO}	Fault output pulse width	$C_{FO}=22\text{nF}$ (Note 4)	1.6	2.4	-	ms	
I_{IN}	Input current	$V_{IN} = 5\text{V}$	0.70	1.00	1.50	mA	
$V_{th(on)}$	ON threshold voltage	Applied between U_P , V_P , W_P , U_N , V_N , W_N-V_{NC}	-	-	3.5	V	
$V_{th(off)}$	OFF threshold voltage		0.8	-	-		
V_{OT}	Temperature output	LVIC temperature = 85 $^\circ\text{C}$ (Note 5)	3.57	3.63	3.69	V	

Note 3: Short circuit protection detects sense current divided from main current at N-side IGBT and works for N-side IGBT only. In the case that outer shunt resistor is inserted into main current path, protection current level I_{SC} changes. For details, please refer the application note for this DIIPM.

4: Fault signal is output when short circuit or N-side control supply under-voltage protection works. The fault output pulse-width t_{FO} depends on the capacitance of C_{FO} . ($C_{FO}(\text{typ.}) = t_{FO} \times (9.1 \times 10^{-6})$ [F])

5: DIIPM doesn't shut down IGBTs and output fault signal automatically when temperature rises excessively. When temperature exceeds the protective level that user defined, controller (MCU) should stop the DIIPM immediately. This output might exceed 5V when temperature rises excessively, so it is recommended to insert a clamp Di between controller supply (e.g. 5V) and V_{OT} output for overvoltage protection. Temperature of LVIC vs. V_{OT} output characteristics is described in Fig.2

Fig. 2 Temperature of LVIC vs. V_{OT} Output Characteristics



Please refer the application note about the usage of V_{OT} too.

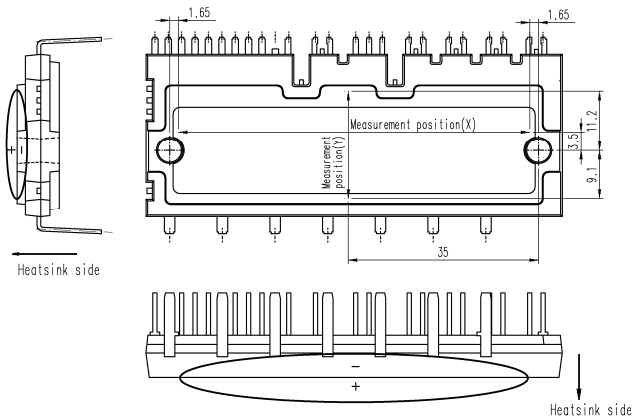
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MECHANICAL CHARACTERISTICS AND RATINGS

Parameter	Condition		Limits			Unit
			Min.	Typ.	Max.	
Mounting torque	Mounting screw : M4	Recommended 1.18N·m	0.98	1.18	1.47	N·m
Terminal pulling strength	Load 19.6N	JEITA-ED-4701	10	-	-	s
Terminal bending strength	Load 9.8N, 90deg. bend	JEITA-ED-4701	2	-	-	times
Weight			-	46	-	g
Heat-sink flatness		(Note 6)	-50	-	100	μm

Note 6: Measurement point of heat-sink flatness



RECOMMENDED OPERATION CONDITIONS

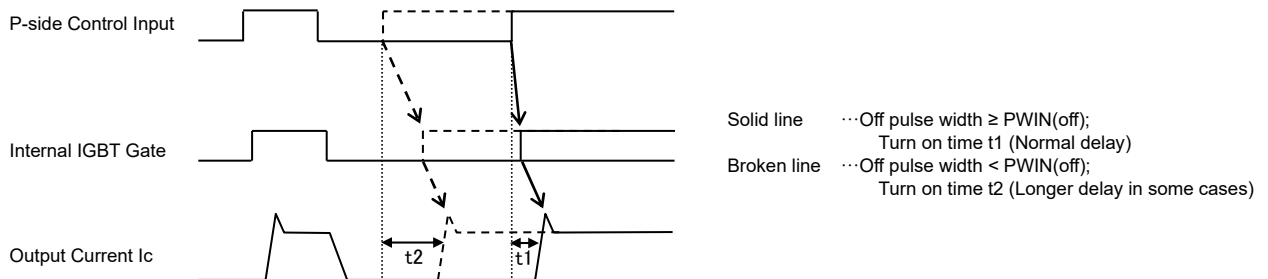
Symbol	Parameter	Condition	Limits			Unit	
			Min.	Typ.	Max.		
V_{CC}	Supply voltage	Applied between P-NU, NV, NW	350	600	800	V	
V_D	Control supply voltage	Applied between V_{P1} - V_{PC} , V_{N1} - V_{NC}	13.5	15.0	16.5	V	
V_{DB}	Control supply voltage	Applied between V_{UFB} - V_{UFS} , V_{VFB} - V_{VFS} , V_{WFB} - V_{WFS}	13.0	15.0	18.5	V	
$\Delta V_D, \Delta V_{DB}$	Control supply variation		-1	-	+1	V/μs	
t_{dead}	Arm shoot-through blocking time	For each input signal	3.0	-	-	μs	
f_{PWM}	PWM input frequency	$T_C \leq 100^\circ\text{C}$, $T_J \leq 125^\circ\text{C}$	-	-	20	kHz	
I_O	Allowable r.m.s. current	$V_{CC} = 600\text{V}$, $V_D = 15\text{V}$, P.F = 0.8, Sinusoidal PWM $T_C \leq 100^\circ\text{C}$, $T_J \leq 125^\circ\text{C}$ (Note 7)	$f_{PWM} = 5\text{kHz}$	-	-	13.7	Arms
			$f_{PWM} = 15\text{kHz}$	-	-	9.2	
PWIN(on)		(Note 8)	1.5	-	-	μs	
PWIN(off)	Minimum input pulse width	$350 \leq V_{CC} \leq 800\text{V}$, $13.5 \leq V_D \leq 16.5\text{V}$, $13.0 \leq V_{DB} \leq 18.5\text{V}$, $-20^\circ\text{C} \leq T_C \leq 100^\circ\text{C}$, N line wiring inductance less than 10nH (Note 9)	$I_C \leq 25\text{A}$	2.3	-		-
			$25\text{A} < I_C \leq 42.5\text{A}$	2.9	-	-	
V_{NC}	V_{NC} variation	Between V_{NC} -NU, NV, NW (including surge)	-5.0	-	+5.0	V	
T_J	Junction temperature		-20	-	+125	°C	

Note 7: The allowable r.m.s. current value depends on the actual application conditions.

Note 8: DIIPM might not make response to the input on signal with pulse width less than PWIN (on).

Note 9: IPM might make no response or delayed response (P-side IGBT only) for the input signal with off pulse width less than PWIN(off). Please refer Fig. 3 about delayed response.

Fig. 3 About Delayed Response Against Shorter Input Off Signal Than PWIN(off) (P-side only)

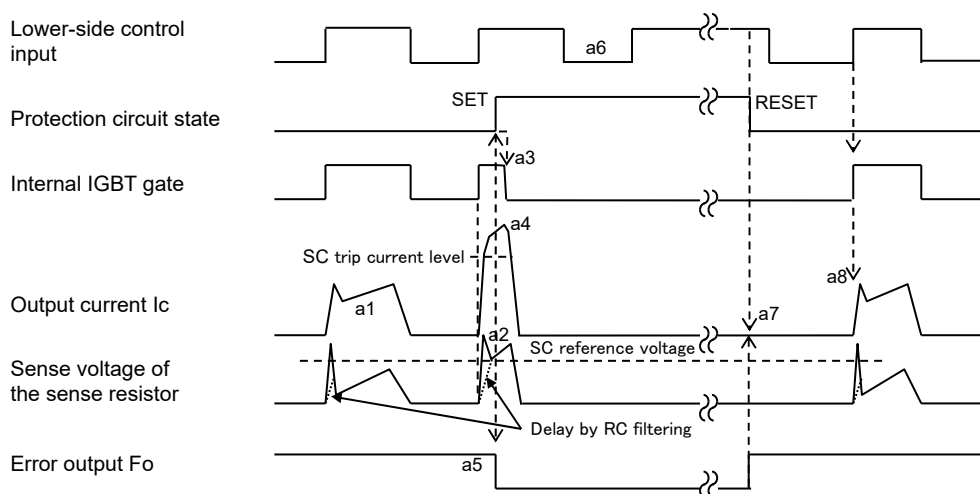


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Fig. 4 Timing Charts of DIIPM Protective Functions

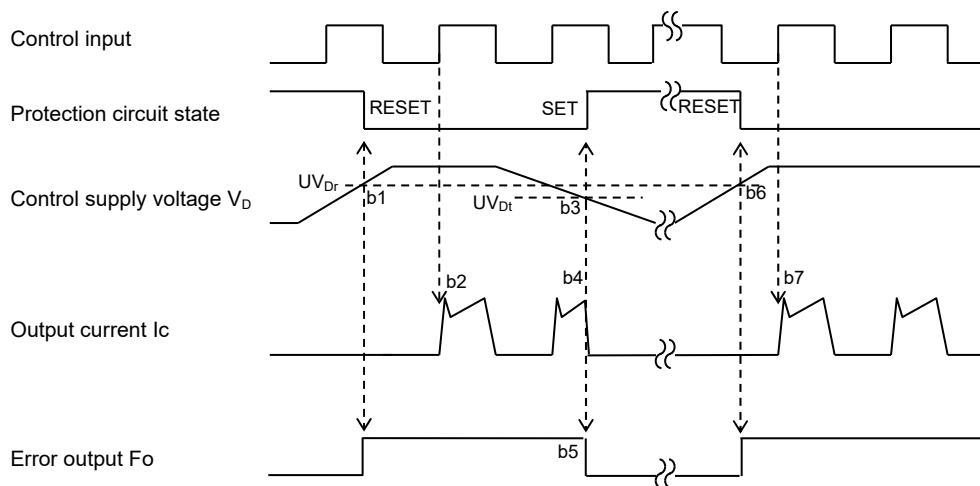
[A] Short-Circuit Protection (N-side only with the external sense resistor and RC filter)

- a1. Normal operation: IGBT ON and outputs current.
- a2. Short circuit current detection (SC trigger)
 (It is recommended to set RC time constant 1.5~2.0 μ s so that IGBT shut down within 2.0 μ s when SC occurs.)
- a3. All N-side IGBT's gates are hard interrupted.
- a4. All N-side IGBTs turn OFF.
- a5. F_O outputs with a fixed pulse width determined by the external capacitor C_{FO}.
- a6. Input = "L": IGBT OFF
- a7. Fo finishes output, but IGBTs don't turn on until inputting next ON signal (L→H).
- (IGBT of each phase can return to normal state by inputting ON signal to each phase.)
- a8. Normal operation: IGBT ON and outputs current.



[B] Under-Voltage Protection (N-side, UV_D)

- b1. Control supply voltage V_D exceeds under voltage reset level (UV_{Dr}), but IGBT turns ON by next ON signal (L→H).
 (IGBT of each phase can return to normal state by inputting ON signal to each phase.)
- b2. Normal operation: IGBT ON and outputs current.
- b3. V_D level drops to under voltage trip level. (UV_{Dt}).
- b4. All N-side IGBTs turn OFF in spite of control input condition.
- b5. F_O outputs for the period determined by the capacitance C_{FO}, but output is extended during V_D keeps below UV_{Dr}.
- b6. V_D level reaches UV_{Dr}.
- b7. Normal operation: IGBT ON and outputs current by next ON signal (L→H).



[C] Under-Voltage Protection (P-side, UV_{DB})

- c1. Control supply voltage V_{DB} rises. After the voltage reaches under voltage reset level UV_{DBr} , IGBT turns on by next ON signal (L→H).
- c2. Normal operation: IGBT ON and outputs current.
- c3. V_{DB} level drops to under voltage trip level (UV_{DBt}).
- c4. IGBT of corresponding phase only turns OFF in spite of control input signal level, but there is no F_o signal output.
- c5. V_{DB} level reaches UV_{DBr} .
- c6. Normal operation: IGBT ON and outputs current by next ON signal (L→H).

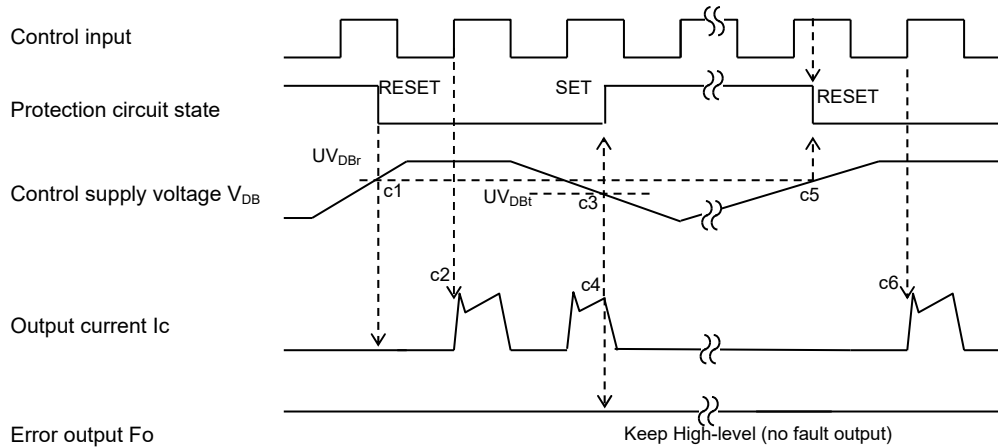
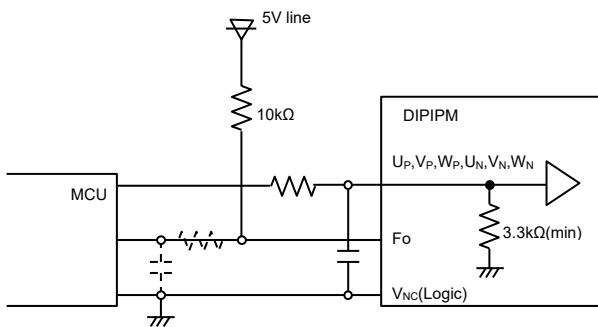


Fig. 5 MCU I/O Interface Circuit

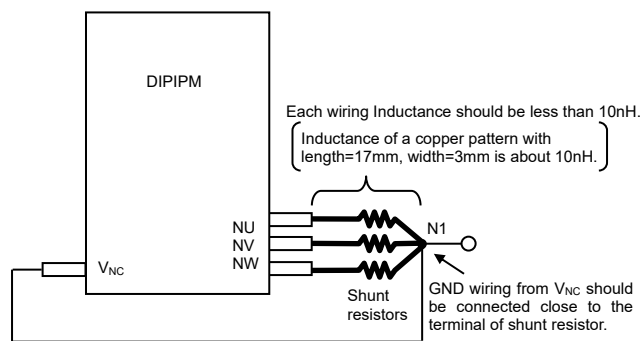


Note)

Design for input RC filter depends on the PWM control scheme used in the application and the wiring impedance of the printed circuit board. But because noisier in the application for 1200V, it is strongly recommended to insert RC filter. (Time constant: over 100ns. e.g. 100Ω, 1000pF) The DIIPM input signal interface integrates a min. 3.3kΩ pull-down resistor. Therefore, when using RC filter, be careful to satisfy turn-on threshold voltage requirement.

F_o output is open drain type. It should be pulled up to the positive side of 5V or 15V power supply with the resistor that limits F_o sink current I_{F_o} under 1mA. In the case of pulling up to 5V supply, over 5.1kΩ is needed. (10kΩ □ is recommended.)

Fig. 6 Wiring Pattern around the Shunt Resistor in the Case of Inserting into Main Current Path



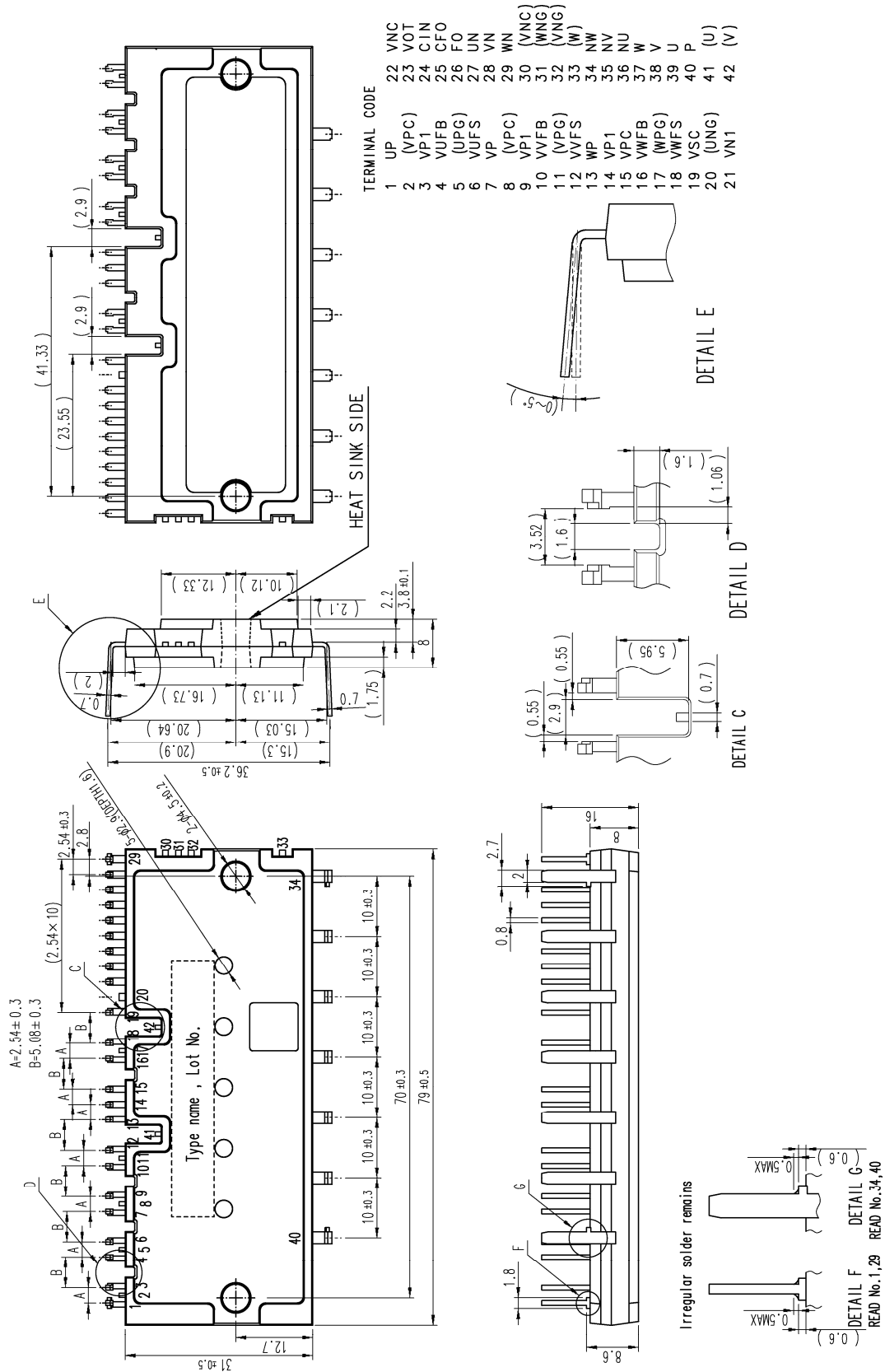
Low inductance shunt resistor like surface mounted (SMD) type is recommended. Protection current level I_{sc} changes by inserting shunt resistor.

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Fig. 8 Package Outlines

Dimensions in mm



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